DATASHEET

Chip Phototransistor With Right Angle Lens PT12-21C/TR8

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Features

- Fast response time
- High photo sensitivity
- Small junction capacitance
- Package in 8mm tape on 7" diameter reels.
- The product itself will remain within RoHS compliant version.
- Pb free
- Compliance with EU REACH

Descriptions

- PT12-21C/TR8 is a phototransistor in miniature SMD package which is molded in a water clear with right angle lens.
- The device is Spectrally matched to visible and infrared emitting diode.

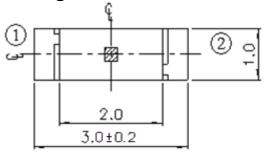
Applications

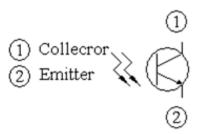
- Miniature switch
- Counters and sorter
- Position sensor
- Infrared applied system

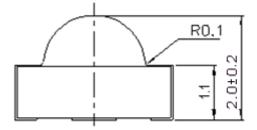
Device Selection Guide

Part Category	Chip Material	Lens Color
PT	Silicon	Water clear

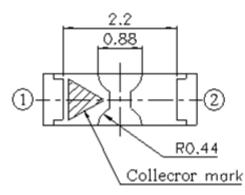
Package Dimensions

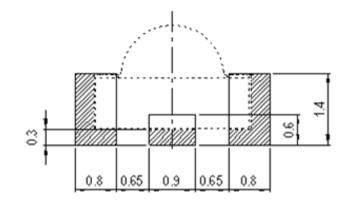






For reflow soldering (propose)





Notes: 1.All dimensions are in millimeters

- 2. Tolerances unless dimensions ±0.1mm
- 3.Suggested pad dimension is just for reference only Please modify the pad dimension based on individual need

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Rating	Units	
Collector-Emitter Voltage	V_{CEO}	30	V	
Emitter-Collector-Voltage	V_{ECO}	5	V	
Collector Current	I _C	50	mA	
Operating Temperature	T _{opr}	-25 ~ +85	°C	
Storage Temperature	T _{stg}	-40 ~ +85	°C	
Soldering Temperature	T _{sol}	260	°C	
Power Dissipation at(or below) 25°C Free Air Temperature	P _d	75	mW	

Notes: *1:Soldering time \leq 5 seconds.

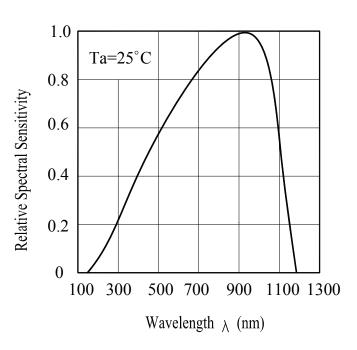
Electro-Optical Characteristics (Ta=25°C)

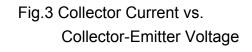
Parameter	Symbol	Condition	Min.	Тур.	Max.	Units
Rang Of Spectral Bandwidth	λ _{0.5}		400		1100	nm
Wavelength Of Peak Sensitivity	λ _P			940		nm
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =100µA Ee=0mW/cm²	30			V
Emitter-Collector Breakdown Voltage	BV _{ECO}	I _E =100μA Ee=0mW/cm²	5			V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =2mA Ee=1mW/cm ²			0.4	V
Collector Dark Current	I _{CEO}	V _{CE} =20V Ee=0mW/cm ²			100	nA
On State Collector Current	I _{C(ON)}	V _{CE} =5V Ee=1mW/cm ²	0.3	1.14		mA

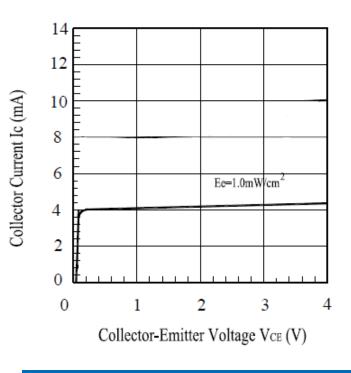
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Typical Electro-Optical Characteristics Curves

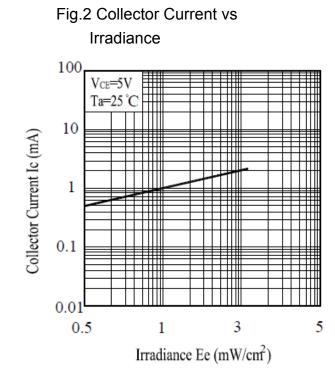
Fig.1 Spectral Sensitivity







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Precautions For Use

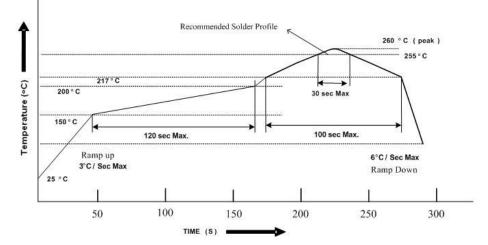
1. Over-current-proof

Customer must apply resistors for protection, otherwise slight voltage shift will cause big current change (Burn out will happen).

- 2. Storage
 - 2.1 Do not open moisture proof bag before the products are ready to use.
 - 2.2 Before opening the package, the Phototransistor should be kept at 10°C ~30°C and 90%RH or less.
 - 2.3 The Phototransistor suggested be used within one year.
 - 2.4 After opening the package, the devices must be stored at 10°C~30°C and ≤ 60%RH, and used within 168 hours (floor life). If unused Phototransistor remain, it should be stored in moisture proof packages.
 - 2.5 If the moisture absorbent material (desiccant material) has faded or unopened bag ha exceeded the shelf life or devices (out of bag) have exceeded the floor life, baking treatment is required.
 - 2.6 If baking is required, refer to IPC/JEDEC J-STD-033 for bake procedure or recommend the following conditions:

96 hours at 60°C ± 5°C and < 5 % RH (reeled/tubed/loose units)

- 3. Soldering Condition
 - 3.1 Pb-free solder temperature profile



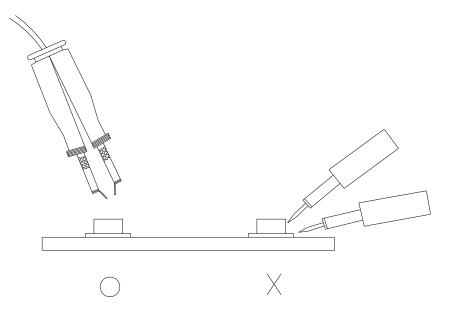
- 3.2 Reflow soldering should not be done more than two times.
- 3.3 When soldering, do not put stress on the Phototransistor during heating.
- 3.4 After soldering, do not warp the circuit board.

4.Soldering Iron

Each terminal is to go to the tip of soldering iron temperature less than 350° C for 3 seconds within once in less than the soldering iron capacity 25W. Leave two seconds and more intervals, and do soldering of each terminal. Be careful because the damage of the product is often started at the time of the hand solder.

5.Repairing

Repair should not be done after the Phototransistor have been soldered. When repairing is unavoidable, a double-head soldering iron should be used (as below figure). It should be confirmed beforehand whether the characteristics of the Phototransistor will or will not be damaged by repairing.

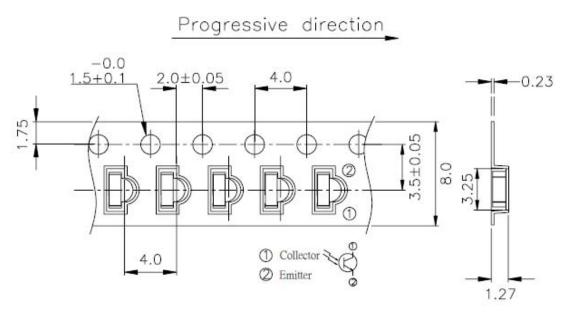


Package Dimensions



Note: The tolerances unless mentioned are ±0.1mm, Unit: mm

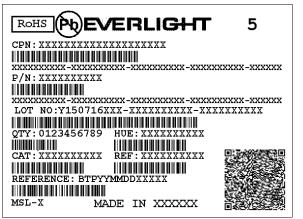
Carrier Taping Dimensions: (Quantity: 2000PCS/Reel)



Note: The tolerances unless mentioned are ±0.1mm, Unit: mm **Label Form Specification**

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CPN: Customer's Production Number P/N : Production Number QTY: Packing Quantity CAT: Ranks HUE: Peak Wavelength REF: Reference LOT No: Lot Number MSL-X: MSL Level Made In: Manufacture place

Notes

- 1. Above specification may be changed without notice. EVERLIGHT will reserve authority on material change for above specification.
- 2. The graphs shown in this datasheet are representing typical data only and do not show guaranteed values.
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EVERLIGHT ELECTRONICS CO., LTD. Office: No. 6-8, Zhonghua Rd., Shulin Dist., New Taipei City 23860, Taiwan Tel: 886-2-2685-6688 Fax: 886-2685-2699 [,] 6897

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